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L Number	Hits	Search Text	DB	Time stamp
- Number	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO;	2002/03/18 17:55
-	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/03/18 17:55
٠	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/03/18
_	60	MOSFET\$1)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	17:55
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
-	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
-	2/19	lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
-	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
-	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	8141	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58

	9373	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-MOSFET\$1 or LD-NMOSFET\$1 o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:02
	152308	drain\$1	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	18:35
_	140917	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
	1922	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15

			_	
-	15865	(amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/18 18:04
-	39181	(amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/15 18:05
-	30917	(amorphous or amorph\$9) near3 film\$1	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/15 18:11
_	67049	((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/15 18:11
	204	<pre>near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1) (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3))</pre>	DERWENT; IBM_TDB USPAT;	2002/03/15
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1) or (lateral\$4 near7 (MOS or MOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj PMOS\$2 or (LD adj PMOS\$2) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$2) or LD-NMOS\$2 or (LD adj NMOS\$2) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$2) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))) and ((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	18:12
_	5147	near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:07

		_		
	69	((((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)	USPAT;	2002/03/15
-	69	or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	US-PGPUB;	18:25
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj	EPO; JPO;	_
		metal adj oxide adj semiconduct\$4) or	DERWENT;	
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	IBM TDB	
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or	1011_100	
1		MOSFETSI)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		1
	Ì	((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		` I
		(lateral\$4 adj double adj diffus\$5 adj		
	1	(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
	ļ	(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
į		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or	ļ	ĺ
	İ	(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1)))) and ((gate\$1 or		Į.
		electrode\$1) and source\$1 and drain\$1)		
	İ	and ((field adj (oxide\$1 or isolat\$5)) or		L.
		LOCOS\$2 or trench\$2 or STI\$1 or (shallow		
		adj trench\$2 adj isolat\$5))) and		
		(((amorphous or amorph\$9) near3 (region\$1		
		or area\$1 or part\$1 or portion\$1 or		
		element\$1)) or ((amorphous or amorph\$9)		
		near3 (layer\$1 or substrate\$1 or		
		wafer\$1)) or ((amorphous or amorph\$9)		1
		near3 film\$1))) and (implant\$8 adj	İ	
		(silicon or Si or "Si" or Ge or "Ge" or		
		germanium))		
_	498	(((amorphous or amorph\$9) near3 (region\$1	USPAT;	2002/03/15
		or area\$1 or part\$1 or portion\$1 or	US-PGPUB;	18:47
		element\$1)) or ((amorphous or amorph\$9)	EPO; JPO;	
	1	near3 (layer\$1 or substrate\$1 or	DERWENT;	
		wafer\$1)) or ((amorphous or amorph\$9)	IBM_TDB	
1	1	near3 film\$1)) same (implant\$8 adj		
		(silicon or Si or "Si" or Ge or "Ge" or		
		germanium))		
1	1	yezmanı am/	<u> </u>	<u></u>

		(1/ 20002)	ticDAT.	2002/03/15
	30	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)	USPAT; US-PGPUB;	18:26
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	EPO; JPO;	10.20
	1	MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj	DERWENT;	1
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	IBM_TDB	
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		1
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		1
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		ļ
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		1
		(lateral\$4 adj double-diffus\$5 adj metal		
		ladi oxide adi semiconduct\$4)) or		
	1	(lateral\$4 adj double adj diffus\$5 ad]		
		(MOSS3 or MOSFET\$1)) or (lateral\$4 near/		
		(metal adj oxide adj semiconduct\$4)) or	[\
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		<u> </u>
	İ	or NMOSFETS1 or PMOS or PMOSFETS1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
l		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
İ		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
Į.		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		Ì
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		1
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1)))) and ((((amorphous or		
ļ		amorph\$9) near3 (region\$1 or area\$1 or	1	
		part\$1 or portion\$1 or element\$1)) or	1	
		((amorphous or amorph\$9) near3 (layer\$1		
ì		or substrate\$1 or wafer\$1)) or		
1		((amorphous or amorph\$9) near3 film\$1))		
1	}	same (implant\$8 adj (silicon or Si or	1	1
}	1	"Si" or Ge or "Ge" or germanium)))	USPAT;	2002/03/15
\ -	330	(((amorphous or amorph\$9) near3 (region\$1	US-PGPUB;	18:47
		or area\$1 or part\$1 or portion\$1 or	EPO; JPO;	1 20.11
		element\$1)) or ((amorphous or amorph\$9)	DERWENT;	
		near3 (layer\$1 or substrate\$1 or	IBM TDB	
	1	wafer\$1)) or ((amorphous or amorph\$9)	1 DFI _ 1 D D	
		near3 film\$1)) with (implant\$8 adj		1
		(silicon or Si or "Si" or Ge or "Ge" or		
1		germanium))		

	22	((((amorphous or amorph\$9) near3	USPAT;	2002/03/15
	""	(region\$1 or area\$1 or part\$1 or	US-PGPUB;	18:50
		portion\$1 or element\$1)) or ((amorphous	EPO; JPO;	2000
		or amorph\$9) near3 (layer\$1 or	DERWENT;	
		substrate\$1 or wafer\$1)) or ((amorphous	IBM TDB	
		1 · · · · · · · · · · · · · · · · · · ·	IBM_IDB	
	1	or amorph\$9) near3 film\$1)) with		
	1	(implant\$8 adj (silicon or Si or "Si" or		
		Ge or "Ge" or germanium))) and ((LDMOS\$2		
		or LD-MOS\$2 or (LD adj MOS\$3) or		
		LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or	ļ	
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
·		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
	1	(insulat\$5 adj gate adj field adj effect		
	22501	adj transistor\$1)))	IIGD N m -	2002/02/15
-	23681	(((amorphous or amorph\$9) near3 (region\$1	USPAT;	2002/03/15
		or area\$1 or part\$1 or portion\$1 or	US-PGPUB;	18:51
		element(1)) or ((amorphous or amorph(9))	EPO; JPO;	
		near3 (layer\$1 or substrate\$1 or	DERWENT;	
		wafer\$1)) or ((amorphous or amorph\$9)	IBM_TDB	
		near3 film\$1)) with (substrate or wafer)		, _ ,
-	244	(implant\$8 adj (silicon or Si or "Si" or	USPAT;	2002/03/15
		Ge or "Ge" or germanium)) same	US-PGPUB;	18:51
		((((amorphous or amorph\$9) near3	EPO; JPO;	
		(region\$1 or area\$1 or part\$1 or	DERWENT;	
		portion\$1 or element\$1)) or ((amorphous	IBM_TDB	
		or amorph\$9) near3 (layer\$1 or	=	
		substrate\$1 or wafer\$1)) or ((amorphous		
1		or amorph\$9) near3 film\$1)) with		
		(substrate or wafer))		

			, 	
–	16	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)	USPAT;	2002/03/15
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	US-PGPUB;	18:52
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj	EPO; JPO;	
		metal adj oxide adj semiconduct\$4) or	DERWENT;	
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	IBM_TDB	
	1	MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
1		(lateral\$4 adj double-diffus\$5 adj metal		
		(lateral 34 adj double-dillus 35 adj metal		
	İ	adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
1		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS	:	
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or	İ	Ī
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		•
	1	or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
1	 	(LD adj NMOS\$3) or LDNMOSFET\$1 or	1	
1		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or	1	
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		1
		(insulats adj gate adj fleid adj effect		
İ		adj transistor\$1)))) and ((implant\$8 adj		
		(silicon or Si or "Si" or Ge or "Ge" or		
		<pre>germanium)) same ((((amorphous or</pre>		
1		amorph\$9) near3 (region\$1 or area\$1 or		
		part\$1 or portion\$1 or element\$1)) or		
		((amorphous or amorph\$9) near3 (layer\$1		
•		or substrate\$1 or wafer\$1)) or		
		((amorphous or amorph\$9) near3 film\$1))		ļ
		with (substrate or wafer)))		
1_	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or	USPAT;	2002/03/18
	/20	LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	US-PGPUB;	17:55
			EPO; JPO;	
		MOSFET\$1)	DERWENT;	ļ.
			IBM TDB	
		7 . 304 34 345505	_	2002/03/18
-	51	lateral\$4 adj diffus\$5 adj metal adj	USPAT;	· · ·
		oxide adj semiconduct\$4	US-PGPUB;	17:55
		•	EPO; JPO;	1
			DERWENT;	
1			IBM_TDB	2000/03/10
-	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or	USPAT;	2002/03/18
		MOSFET\$1)	US-PGPUB;	17:56
1			EPO; JPO;	ļ
			DERWENT;	
			IBM_TDB	
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)	USPAT;	2002/03/18
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD	US-PGPUB;	17:56
		adj MOSFET\$1)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1_	74	(lateral\$4 adj double adj diffus\$5 adj	USPAT;	2002/03/18
-	'4	metal adj oxide adj semiconduct\$4) or	US-PGPUB;	17:56
		(lateral\$4 adj double-diffus\$5 adj metal	EPO; JPO;	
	ļ	adj oxide adj semiconduct\$4)	DERWENT;	
	1	adj oxide adj semiconducca4)	IBM_TDB	
	1	2 4 244 24 2 22 2 24 2 25 45 47		2002/03/18
-	178		USPAT;	
	1	(MOS\$3 or MOSFET\$1)	US-PGPUB;	17:56
			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	1
-	250	lateral\$4 near7 (metal adj oxide adj	USPAT;	2002/03/18
	1	semiconduct\$4)	US-PGPUB;	17:57
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	

		_		
_	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
_	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59
	9374	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj PMOS\$2) or (LD adj NMOSFET\$1) or (LD adj NMOSFET\$1 or LD-NMOSFET\$1 or LD-NMOSFET\$1 or CLD adj NMOSFET\$1 or LD-NMOSFET\$1 or LD-	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:03
_	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44

				0000/02/10
-		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or Infertal\$4 adj8 (MOS or MOSFET\$1 or Infertal\$4 adj8 (MOS o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:06
-	. 5148	adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)) implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/18 18:13
-	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09
-	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22
_	7645	<pre>implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24
	26134	<pre>(implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25

	100	// 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	HCDDW.	2002/03/18
-	176	((implant\$8 adj (silicon or Si or "Si" or	USPAT; US-PGPUB;	18:25
Į.		Ge or "Ge" or germanium)) or (implant\$8		10.25
İ		near8 (silicon or Si or "Si" or Ge or	EPO; JPO;	
		"Ge" or germanium)) or (implant\$8 with	DERWENT;	
		((silicon or Si or "Si" or Ge or "Ge" or	IBM_TDB	
ĺ		germanium) near2 (ion\$1 or atom\$1)))) and		
		(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	:	
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
	ļ	(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
	ì	MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
1		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or	!	
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
1		or NMOSFET\$1 or PMOS or PMOSFET\$1 or	1	
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1)))) and ((amorphous or		
		amorph\$9) same (substrate or wafer)))	1	
-	152356	(gate\$1 or electrode\$1) and source\$1 and	USPAT;	2002/03/18
		drain\$1	US-PGPUB;	18:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	141012	(field adj (oxide\$1 or isolat\$5)) or	USPAT;	2002/03/18
		LOCOS\$2 or trench\$2 or STI\$1 or (shallow	US-PGPUB;	18:37
		adj trench\$2 adj isolat\$5)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	120	(((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	18:38
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1	_	
	1	or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2		
		or (LD adj MOS\$3) or LDMOSFET\$1 or	,	
		LD-MOSFET\$1 or (LD adj MOSFET\$1)) or		İ
		(lateral\$4 adj diffus\$5 adj metal adj		
		oxide adj semiconduct\$4) or (lateral\$4		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
		(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)		
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD		
1		adj MOSFET\$1)) or ((lateral\$4 adj double		
		adj diffus\$5 adj metal adj oxide adj	İ	
		semiconduct\$4) or (lateral\$4 adj		
		double-diffus\$5 adj metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 adj double	ĺ	
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
		(lateral\$4 near7 (metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 near7 (MOS		
		or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS		
		or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2		
		or (LD adj PMOS\$3) or LDPMOSFET\$1 or		İ
		LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or		
		(LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3)		
		or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj		1
	İ	NMOSFET\$1)) or (lateral\$4 near7 (DMOS or		ì
		DMOSFET\$1)) or (lateral\$4 adj8 (MOS or		
		MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or		
		PMOSFET\$1 or FET\$1 or transistor\$1 or		
		IGFET\$1 or (insulat\$5 adj gate adj field		
		adj effect adj transistor\$1)))) and		
		((amorphous or amorph\$9) same (substrate		
		or wafer)))) and ((field adj (oxide\$1 or		
		isolat\$5)) or LOCOS\$2 or trench\$2 or		
		STI\$1 or (shallow adj trench\$2 adj		
		isolat\$5))		

-	1255	((implant\$8 adj (silicon or Si or "Si" or	USPAT;	2002/03/18
		Ge or "Ge" or germanium)) or (implant\$8	US-PGPUB;	18:44
		near8 (silicon or Si or "Si" or Ge or	EPO; JPO;	
		"Ge" or germanium)) or (implant\$8 with	DERWENT;	
		((silicon or Si or "Si" or Ge or "Ge" or	IBM_TDB	
		germanium) near2 (ion\$1 or atom\$1)))) and		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
[metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal	İ	
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		<pre>(insulat\$5 adj gate adj field adj effect adj transistor\$1))))</pre>]
	200		HSDAT.	2002/03/18
-	280	(((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
_	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or	US-PGPUB;	2002/03/18 18:45
_	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si"	US-PGPUB; EPO; JPO;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si"	US-PGPUB; EPO; JPO;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	<pre>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or</pre>	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 or MOSFET\$1)) or	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj moSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj moSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1)) or ((lateral\$4 adj double	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDMOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj semiconduct\$4)) or (lateral\$4 adj double	US-PGPUB; EPO; JPO; DERWENT;	· · ·
	280	<pre>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or</pre>	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDMOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj semiconduct\$4)) or (lateral\$4 adj double	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$5) or LDDMOSFET\$1 or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or	US-PGPUB; EPO; JPO; DERWENT;	' '
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	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj moSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or LD-PMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3)	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj moSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1)) or (LDNMOSFET\$1)) or (LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (LDNMOSFET\$1)) or (LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (LDNMOSFET\$1)) or (LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (LDNMOSFE	US-PGPUB; EPO; JPO; DERWENT;	' '
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	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or LD-PMOS\$3) or LDPMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or NMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS	US-PGPUB; EPO; JPO; DERWENT;	' '
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	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or LDDMOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or (LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or LD-PMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or LD adj NMOSFET\$1 or LD-NMOSFET\$1 or LD adj NMOSFE	US-PGPUB; EPO; JPO; DERWENT;	' '
	280	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3) or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or (LDD adj MOSFET\$1)) or (LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or DMOS or DMOSFET\$1 or LD-PMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or DMOSFET\$1 or FET\$1 or transistor\$1 or	US-PGPUB; EPO; JPO; DERWENT;	' '

2002/03/18 (((implant\$8 adj (silicon or Si or "Si" USPAT; US-PGPUB; 19:54 or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" EPO; JPO; DERWENT; or Ge or "Ge" or germanium)) or IBM_TDB (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) or ((((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))) and (amorphous or amorph\$9))

				10000100100
-	848	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or amorph\$9) with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18
	45	(substrate or wafer) (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) with (amorphous or amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1) or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOS\$3) or LDPMOSFET\$1) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj PMOSFET\$1)) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj PMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
-	1853	or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) ((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8	USPAT; US-PGPUB;	2002/03/18 19:58
		near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))))	EPO; JPO; DERWENT; IBM_TDB	

-	78	(((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	19:58
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1	_	
		or atom\$1)))) same (amorphous or		
		amorph\$9) same (substrate or wafer)) and		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
İ		metal adj oxide adj semiconduct\$4) or		l
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		1
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		1
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
	·	(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj	ļ	
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 hear/ (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1))))		
_	43237	(crystall\$9 or re-crystall\$9 or (re adj	USPAT;	2002/03/18
		crystall\$9)) with amorph\$9	US-PGPUB;	21:53
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	8629	gaussian with (distribut\$6 or profil\$4)	USPAT;	2002/03/18
		-	US-PGPUB;	21:55
	}	•	EPO; JPO;	
			DERWENT;	
			IBM TDB	

	3	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
	_	or Ge or "Ge" or germanium)) or	US-PGPUB;	21:56
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	<u> </u>
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1	_	
		or atom\$1)))) with (amorphous or		
		amorph\$9) with (substrate or wafer)) and		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj	ĺ	1
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		ļ
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		-
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		1
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		1
		adj transistor\$1))))) and ((crystall\$9 or		
1		re-crystall\$9 or (re adj crystall\$9))		
		with amorph\$9) and (gaussian with		
		(distribut\$6 or profil\$4))	<u> </u>	

_ 3	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
-	or Ge or "Ge" or germanium)) or	US-PGPUB;	21:56
	(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
į	or Ge or "Ge" or germanium)) or	DERWENT;	
	(implant\$8 with ((silicon or Si or "Si"	IBM TDB	
	or Ge or "Ge" or germanium) near2 (ion\$1	1511_155	
	or atom\$1)))) same (amorphous or		
	amorph\$9) same (substrate or wafer)) and		
	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
	or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
	MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
	metal adj oxide adj semiconduct\$4) or		
	(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
Į	MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
	(LDD adj MOS\$3) or LDDMOSFET\$1 or	1	
	LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
	((lateral\$4 adj double adj diffus\$5 adj		
ļ	metal adj oxide adj semiconduct\$4) or		
1	(lateral\$4 adj double-diffus\$5 adj metal		
	adj oxide adj semiconduct\$4)) or		
	(lateral\$4 adj double adj diffus\$5 adj		
	(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		1
	(metal adj oxide adj semiconduct\$4)) or		
	(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
	or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
	(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
	or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
	PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
	(LD adj NMOS\$3) or LDNMOSFET\$1 or		
	LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
	(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
	(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
	or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
	FET\$1 or transistor\$1 or IGFET\$1 or		
	(insulat\$5 adj gate adj field adj effect		
	adj transistor\$1))))) and ((crystall\$9 or		
	re-crystall\$9 or (re adj crystall\$9))		
	with amorph\$9) and (gaussian with		
	(distribut\$6 or profil\$4))		

	6	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
1	ł	or Ge or "Ge" or germanium)) or	US-PGPUB;	21:58
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	1
		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	
ļ		or Ge or "Ge" or germanium) near2 (ion\$1		
		or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2		
		or (LD adj MOS\$3) or LDMOSFET\$1 or		ì
		LD-MOSFET\$1 or (LD adj MOSFET\$1)) or		
		(lateral\$4 adj diffus\$5 adj metal adj		
		oxide adj semiconduct\$4) or (lateral\$4		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
}		(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)		
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD		
		adj MOSFET\$1)) or ((lateral\$4 adj double		<u> </u>
		adj diffus\$5 adj metal adj oxide adj		
		semiconduct\$4) or (lateral\$4 adj		i
		double-diffus\$5 adj metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 adj double		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		1
		(lateral\$4 near7 (metal adj oxide adj		
l	l	semiconduct\$4)) or (lateral\$4 near7 (MOS		
		or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS		ļ
		or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2]	
		or (LD adj PMOS\$3) or LDPMOSFET\$1 or]
		LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or		
		(LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3)		
		or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj		
		NMOSFET\$1)) or (lateral\$4 near7 (DMOS or		
		DMOSFET\$1)) or (lateral\$4 adj8 (MOS or		1
		MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or		
	İ	PMOSFET\$1 or FET\$1 or transistor\$1 or		
	i	IGFET\$1 or (insulat\$5 adj gate adj field		
		adj effect adj transistor\$1)))) and		
		((amorphous or amorph\$9) same (substrate		
		or wafer)))) or ((((implant\$8 adj		
		(silicon or Si or "Si" or Ge or "Ge" or		
		germanium)) or (implant\$8 near8 (silicon		
		or Si or "Si" or Ge or "Ge" or		
		germanium)) or (implant\$8 with ((silicon		
		or Si or "Si" or Ge or "Ge" or germanium)		
		near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2		
		or LD-MOS\$2 or (LD adj MOS\$3) or		
		LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
	,	MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7	1	
				1
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or	1	
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		[
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or	1	1
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or	1	
	[FET\$1 or transistor\$1 or IGFET\$1 or		1
		(insulat\$5 adj gate adj field adj effect	İ	1
		adj transistor\$1))))) and (amorphous or		
		amorph\$9))) and ((crystall\$9 or		
		re-crystalls9 or (re adi crystalls9))		
Search Hi:	tory 1	Pwith amolphis 1 and (gansgrahowith		
		(distribut\$6 or profil\$4))		
	L	(GID CITAGO OF PIOLITAS)	I	<u></u>

	ŧ		
	((((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) with (amorphous or amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or ((lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or ((lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (LD adj NMOSFET\$1) or (LD adj NMOSFET\$1)) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:59
	or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or		
	or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9)		

- 35 ((((implant\$8 adj (silicon or Si or "Si" USPAT; or Ge or "Ge" or germanium)) or US-PGP (implant\$8 near8 (silicon or Si or "Si" EPO; Jor Ge or "Ge" or germanium)) or DERWEN (implant\$8 with ((silicon or Si or "Si" IBM_TD)	UB; 21:59 PO;
or Ge or "Ge" or germanium)) or US-PGP (implant\$8 near8 (silicon or Si or "Si" EPO; J or Ge or "Ge" or germanium)) or DERWEN	PO;
(implant\$8 near8 (silicon or Si or "Si" EPO; Jor Ge or "Ge" or germanium)) or DERWEN	·
or Ge or "Ge" or germanium)) or DERWEN	- · ·
(implant\$8 with ((silicon or Si or "Si" IBM TD	T;
or Ge or "Ge" or germanium) near2 (ion\$1	_
or atom\$1)))) same (amorphous or	
amorph\$9) same (substrate or wafer)) and	
((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)	
or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	
MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj	
metal adj oxide adj semiconduct\$4) or	
(lateral\$4 adj diffus\$5 adj (MOS\$3 or	
MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or	
(LDD adj MOS\$3) or LDDMOSFET\$1 or	
LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or	
((lateral\$4 adj double adj diffus\$5 adj	
metal adj oxide adj semiconduct\$4) or	
(lateral\$4 adj double-diffus\$5 adj metal	
adj oxide adj semiconduct\$4)) or	
(lateral\$4 adj double adj diffus\$5 adj	
(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7	
(metal adj oxide adj semiconduct\$4)) or	
(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS	
or NMOSFET\$1 or PMOS or PMOSFET\$1)) or	
(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)	
or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj	
PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or	
(LD adj NMOS\$3) or LDNMOSFET\$1 or	
LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or	
(lateral\$4 near7 (DMOS or DMOSFET\$1)) or	
(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS	
or NMOSFET\$1 or PMOS or PMOSFET\$1 or	
FET\$1 or transistor\$1 or IGFET\$1 or	
(insulat\$5 adj gate adj field adj effect	
adj transistor\$1))))) and ((crystall\$9 or	
re-crystall\$9 or (re adj crystall\$9))	
with amorph\$9)	
- 1 ("5874768").PN. USPAT;	2002/03/19
US-PGP	PUB 16:21

	4 BRS	3 BRS	2 BRS	1 BRS	Ţ
BRS L7	5 L4	L3	3 L2	, L1	Type L
					#
104	277	79	93	876	Hits
lateral\$4 adj diffus\$5 adj3 metal adj oxide adj semiconduct\$4	(lateral\$4 adj double adj diffus\$5 adj ((metal adj oxide adj semiconduct\$4) or MOS\$2 or MOSFET\$1 or NMOS\$2 or NMOSFET\$1)) or (lateral\$4 adj double-diffus\$5 adj ((metal adj oxide adj semiconduct\$4) or MOS\$2 or MOSFET\$1 or PMOS\$2 or PMOSFET\$1 or NMOS\$2 or PMOSFET\$1 or NMOS\$2 or NMOSFET\$1))	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1 or NMOS or PMOS or NMOSFET\$1 or PMOSFET\$1)	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	Search Text
USPAT; 3 US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2002/10/20	2002/10/20	2002/10/20 13:22	2002/10/20 13:32	2002/10/20 13:20	Time Stamp
					Comme nts
					Error Defini tion
0	0	0	0	0	Err

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comme r	Error Defini	Err
D	BRS	L5	φ	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LD-PMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:33			0
7	BRS	L6	U	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
ω	BRS	81	982	1 or 2 or 3 or 4 or 5 or 6 or 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
9	BRS	L9	160596	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; and US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:38			0
10	BRS	L10	16999	(amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
L L	BRS	L11	41155	(amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
12	BRS	L12	10445	(amorphous or amorph\$9) near3 surfac\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0

0			2002/10/20 14:35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	8 and 15	114	L19	BRS	19
0			2002/10/20 14:35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	8 and 17	V	L18	BRS	18
0			2002/10/20 14:26	UB; PO; T;	15 same 16	2443	L17	BRS	17
0			2002/10/20 14:26	UB; PO; B	10 or 11 or 12	54828	L16	BRS	16
0			2002/10/20 14:44	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)	32605	L15	BRS	15
0			2002/10/20 13:44	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	8 and 9 and (10 or 11 or 12) and 13	9	L14	BRS	14
0			2002/10/20 14:25		implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	5506	L13	BRS	13
Err	Error Defini tion	Comme nts	Time Stamp	DBs	Search Text	Hits	L #	Туре	

	——	Туре	#	Hits	Search Text	DBs	Time	ime Stamp	Stamp Comme
20	0 BRS		L20	2855	(implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)) with (amorphous or amorph\$9)	USPAT; US-PGPU EPO; JP DERWENT IBM_TDB	UB; PO; T;	YT; GPUB; 2002/10/20 JPO; 14:44 JENT; 14:44	
21	1 BRS		L21	3000	implant\$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium) with (amorphous or amorph\$9)	USPAT; US-PGP EPO; J DERWEN IBM_TD	UB; PO; B	AT; PGPUB; 2002/10/20; JPO; 14:50 MENT; 14:50	⊢ N
22	2 BRS	RS	L22	α	8 and 21	USPAT; US-PGP EPO; J DERWEN IBM_TD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	YT; PGPUB; 2002/10/20; JPO; 14:46 WENT; 14:46	Ļ 2
23	3 BRS	RS	L23	3809	(implant\$8 with (silicon or US-PGPUB; Si or "Si" or Ge or "Ge" or EPO; JPO; germanium)) same (amorphous DERWENT; or amorph\$9)	USPAT; US-PGPU EPO; JP DERWENT IBM_TDB	or USPAT; or US-PGPUB; or EPO; JPO; us DERWENT; IBM_TDB	T; GPUB; 2002/10/20 JPO; 14:51 ENT; TDB	ы N
24	4 BRS	RS	L24	10	8 and 23	USPAT; US-PGPU EPO; JP DERWENT IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	T; GPUB; 2002/10/20 JPO; 14:51 ENT; 113:51	⊢ N

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ਯ 	
BRS	Туре
L25	# T
9546	Hits
(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or LD-MOSFET\$1 or LD-MOSFET\$1 or LD-MOSFET\$1 or (LD adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOSFET\$1 or LDD-MOS\$2 or LDD-MOS\$2 or LDD-MOSFET\$1 or LDD-MOSFET\$1 or LDD-MOSFET\$1 or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj oxide adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj adj oxide adj oxide adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1) or (lateral\$4 near7 (MOS or lateral\$4 near7 (MOS or lateral\$4 near7 (MOS or LD-PMOS\$2 or (LD adj pMOS\$3) or LDPMOS\$5 or (LD adj pMOSFET\$1) or (LD adj pMOSFET\$1)) or (LD adj or (LD adj or (LD adj or (LD adj or LDNMOS\$2 or LDNMOS\$2 or (LD adj	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2002/10/20	Time Stamp
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2	2	
7	<u>σ</u>	
BRS	BRS	Туре
L27	L26	#
9546	9 5 4 6	Hits
25 or 26	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj MOSFET\$1) or (LD adj MOSFET\$1) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj oxide adj oxide adj double adj adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj oxide adj semiconduct\$4) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or PMOSFET\$1 or PMOS or LDPMOS\$2 or LDPMOS\$3 or LDPMOS\$2 or LDPMOS\$2 or LDPMOS\$2 or LDPMOS\$2 or LDPMOS\$2	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2002/10/20 14:59	2002/10/20	Time Stamp
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0	0	Err

7								3 5 5 5
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					USPAT;			
		••••••			US-PGPUB;	2002/10/20		
28	BRS	L28	9546	8 or 27	EPO; JPO;	1/-50		0
					DERWENT;	٠		
		•••••			IBM_TDB			
					USPAT;			
		•••••	•••••		US-PGPUB;	2002/10/20		
29	BRS	L29	123	21 and 28	EPO; JPO;	15.01		0
	-	••••	••••		DERWENT;	F (•••••
		•••••	••••••		IBM_TDB			•••••
					USPAT;			
		••••••	•••••		US-PGPUB;			*******
30	BRS	L30	149	23 and 28	EPO; JPO;	15.01		0
_	-				DERWENT;			••••
		•••••	•••••		IBM TDB			